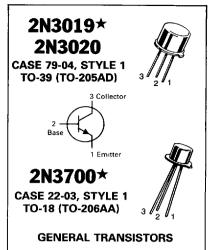
Boca Semiconductor Corp.

MAXIMUM RATINGS

Rating	Symbol	2N3019 2N3020	2N3700	Unit
Collector-Emitter Voltage	VCEO	80	80	Vdc
Collector-Base Voltage	V _{CBO}	140	140	Vdc
Emitter-Base Voltage	VEBO	7.0	7.0	Vdc
Collector Current — Continuous	'c	1.0	1.0	Adc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	0.8 4.6	0.5 2.85	Watts mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	5.0 28.6	1.8 10.6	Watts mW/°C
Operating and Storage Junction Temperature Range	Tj, T _{stg}	-65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	2N3019 2N3020	2N3700	Unit
Thermal Resistance, Junction to Ambient	R _{0JA}	217	350	°C/W
Thermal Resistance, Junction to Case	R ₀ JC	35	97	°C/W



NPN SILICON

★2N3019 and 2N3700 are Motorola designated preferred devices.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				-
Collector-Emitter Breakdown Voltage(1) (Ic = 30 mAdc, Ig = 0)	V(BR)CEO	80	-	Vdc
Collector-Base Breakdown Voltage (I _C = 100 µAdc, I _E = 0)	V(BR)CBO	140	-	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100 \ \mu Adc, I_C = 0$)	V(BR)EBO	7.0		Vdc
Collector Cutoff Current (V _{CB} = 90 Vdc, I _E = 0) (V _{CB} = 90 Vdc, I _E = 0, T _A = +150°C)	ісво	_	0.01 10	μAdc
Emitter Cutoff Current (VEB = 5.0 Vdc, IC = 0)	IEBO	_	0.010	μAdc

ON CHARACTERISTICS

	hFF			
2N3700, 2N3019		50	_	
2N3020		30	100	
2N3700, 2N3019		90	_	
2N3020		40	120	
2N3700, 2N3019		100	300	
2N3020		40	120	
2N3700, 2N3019		40	—	
2N3700, 2N3019		50		
2N3020		30	100	
All Types		15		
	V _{CE(sat)}		_	Vdc
			0.2	
		_	0.5	
	V _{BE(sat)}	_	1.1	Vdc
	1			
	2N3020 2N3700, 2N3019 2N3020 2N3700, 2N3019 2N3700, 2N3019 2N3700, 2N3019 2N3700, 2N3019 2N3700, 2N3019	2N3020 2N3700, 2N3019 2N3020 2N3700, 2N3019 2N3700, 2N3019 2N3700, 2N3019 2N3020 All Types VCE(sat)	2N3700, 2N3019 50 2N3700, 2N3019 30 2N3700, 2N3019 90 2N3700, 2N3019 40 2N3700, 2N3019 100 2N3700, 2N3019 40 2N3700, 2N3019 50 2N3700, 2N3019 50 2N3700, 2N3019 50 All Types 15 VCE(sat) —	2N3700, 2N3019 50 2N3020 30 100 2N3700, 2N3019 90 2N3700, 2N3019 40 120 2N3700, 2N3019 100 300 2N3700, 2N3019 40 2N3700, 2N3019 40 2N3700, 2N3019 50 2N3700, 2N3019 50 2N3700, 2N3019 50 2N3700, 2N3019 50 2N3700 15 VCE(sat) 0.2 0.5

 Current-Gain — Bandwidth Product
 fT
 MHz

 (i_C = 50 mAdc, V_{CE} = 10 Vdc, f = 20 MHz)
 2N3020
 80
 —

 2N3019
 2N3700
 100
 400

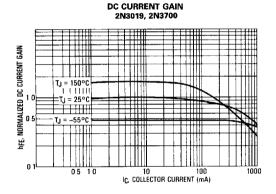
2N3019 2N3020 2N3700

ELECTRICAL CHAI	RACTERISTICS (continued) (T	∆ = 25°0	C unless otherwise noted.)
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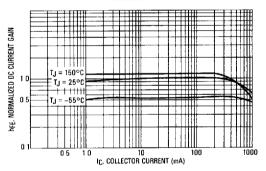
Characteristic		Symbol	Min	Max	Unit
Output Capacitance (V _{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)		C _{obo}	-	12	pF
Input Capacitance (VEB = 0.5 Vdc, I_C = 0, f = 1.0 MHz		C _{ibo}	_	60	pF
Small-Signal Current Gain {I _C = 1.0 mAdc, V _{CE} = 5.0 Vdc, f = 1.0 kHz}	2N3700, 2N3019 2N3020	hfe	80 30	400 200	-
Collector Base Time Constant (IE = 10 mAdc, V_{CB} = 10 Vdc, f = 79.8 MHz)	2N3019, 2N3020 2N3700	rb'C _C	— 15	400 400	ps
Noise Figure ($I_C = 100 \ \mu Adc, V_{CE} = 10 \ Vdc, R_S = 1.0 \ k \ ohms, f = 1.0 \ kHz$)	2N3019, 2N3700	NF	_	4	dB

(1) Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 1.0%.

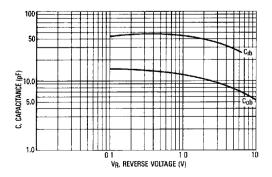
http://www.bocasemi.com



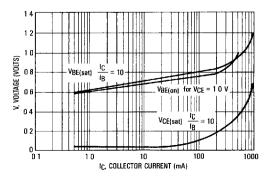
DC CURRENT GAIN 2N3020



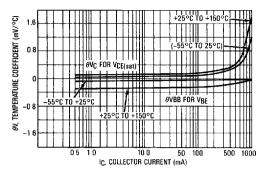
CAPACITANCE



"ON" VOLTAGES

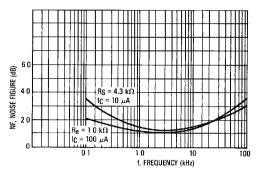


2N3019 2N3020 2N3700

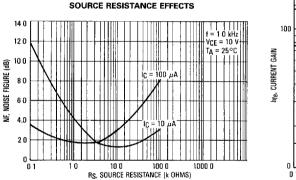


TEMPERATURE COEFFICIENTS

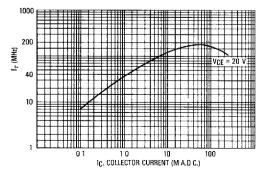
FREQUENCY EFFECTS



CURRENT GAIN BANDWIDTH PRODUCT versus COLLECTOR CURRENT — 1 kHz hfe

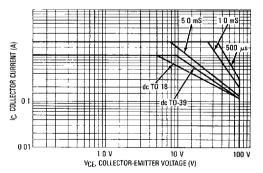


CURRENT GAIN - BANDWIDTH PRODUCT



2N3019 2N3700 2N300 2N3020 2N3020 2N3020 0 10 10 10 10 10 10 10 10 10 10

ACTIVE REGION SAFE OPERATING AREA



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